

## Dimitrios Maroudas – List of PUBLICATIONS

1. D. Maroudas and R. A. Brown, “Diffusion of Point Defects in a Stressed Simple Cubic Crystal,” in *Defects and Diffusion in Semiconductors: Bulk and Layered Structures*, edited by D. J. Wolford, J. Bernholc, and E. E. Haller, *Materials Research Society Symposia Proceedings*, vol. **163**, Materials Research Society, Pittsburgh (1990), pp. 615-620.
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3. D. Maroudas and R. A. Brown, “Analysis of Point Defect Diffusion and Drift in Cubic-Type Lattices: Constitutive Modeling,” *Physical Review B* **44**, 2567-2581 (1991).
4. D. Maroudas and R. A. Brown, “Analysis of the Effects of Oxygen Migration on Dislocation Motion in Silicon,” *Journal of Applied Physics* **69**, 3865-3877 (1991).
5. D. Maroudas and R. A. Brown, “Model of Dislocation Locking by Oxygen Gettering in Silicon Crystals,” *Applied Physics Letters* **58**, 1842-1844 (1991).
6. D. Maroudas and R. A. Brown, “Analysis of Oxygen Gettering and Dislocation Locking in Silicon,” in *Defects in Materials*, edited by P. D. Bristowe, J. E. Epperson, J. E. Griffith, and Z. Liliental-Weber, *Materials Research Society Symposia Proceedings*, vol. **209**, Materials Research Society, Pittsburgh (1991), pp. 597-602.
7. D. Maroudas and R. A. Brown, “Analysis of the Effects of Oxygen on Dislocation Motion in Silicon,” in *Proceedings of the Second Symposium on Defects in Silicon*, edited by W. M. Bullis and U. Gösele, *The Electrochemical Society Proceedings Series*, vol. **91-9**, The Electrochemical Society, Pennington, NJ (1991), pp. 181-188.
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12. D. Maroudas and S. T. Pantelides, “Theoretical Studies of Electromigration in Polycrystalline Metal Stripes,” in *Materials Reliability in Microelectronics III*, edited by K. P. Rodbell, W. F. Filter, H. Frost, and P. S. Ho, *Materials Research Society Symposia Proceedings*, vol. **309**, Materials Research Society, Pittsburgh (1993), pp. 333-338.
13. S. T. Pantelides, D. Maroudas, and D. B. Laks, “Defects in Heterogeneous Solids: From Microphysics to Macrophysics,” *Materials Science Forum* **143**, 1-8 (1994).
14. R. A. Brown, D. Maroudas, and T. Sinno, “Modeling Point Defect Dynamics in the Crystal Growth of Silicon,” *Journal of Crystal Growth* **137**, 12-25 (1994).
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